

NON-VOLATILE MEMORY DEVICE

CROSS-REFERENCE TO RELATED APPLICATION

[0001] Korean Patent Application No. 10-2017-0148320, filed on November 8, 2017, and entitled, “Non-Volatile Memory Device,” is incorporated by reference in its entirety.

TECHNICAL FIELD

[0002] One or more embodiments herein relate to a non-volatile memory device.

BACKGROUND

[0003] A variety of memory devices have been developed to store data. Examples include volatile memory devices and non-volatile memory devices. One type of non-volatile memory device is a flash memory device, which is often used in a mobile phones, digital cameras, portable digital assistant (PDAs), mobile computer devices, stationary computer devices, and other products. A non-volatile memory device typically includes a data output driver having a pull-up driver and a pull-up driver, each of which includes a plurality of transistors.

SUMMARY

[0004] In accordance with one or more embodiments, a non-volatile memory device includes an output driver to output a data signal and including: a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors; and a pull-down driver including a plurality of N-type transistors, wherein one or more power supply voltages having different voltage levels are selectively applied to the pull-up driver and a first power supply voltage is

applied to the first pull-up driver and a second power supply voltage is applied to the second pull-up driver.

[0005] In accordance with one or more other embodiments, a non-volatile memory device includes an output driver to output a data signal; and an operating signal generator to generate a plurality of operating signals for operating the output driver, wherein the output driver includes: a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors; and a pull-down driver having a plurality of N-type transistors, wherein one or more power supply voltages having different voltage levels are to be selectively applied to the pull-up driver.

[0006] In accordance with one or more other embodiments, a non-volatile memory device includes an output driver to output a data signal; and an operating signal generator to generate a plurality of operating signals to operate the output driver, wherein the output driver includes: a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors; and a pull-down driver including a first pull-down driver having a plurality of P-type transistors and a second pull-down driver having a plurality of N-type transistors.

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] Features will become apparent to those of skill in the art by describing in detail exemplary embodiments with reference to the attached drawings in which:

[0008] FIG. 1 illustrates an embodiment of a non-volatile memory device;

[0009] FIG. 2 illustrates an embodiment of a data output circuit;

[0010] FIG. 3 illustrates an embodiment of an output driver;

- [0011] FIGS. 4A and 4B illustrate embodiments of operating mechanisms of a pull-up driver according to voltage levels of a power supply voltage;
- [0012] FIG. 5 illustrates another embodiment of an output driver;
- [0013] FIG. 6 illustrates another embodiment of a data output circuit;
- [0014] FIGS. 7A, 8A, 9A, and 10A illustrate embodiments of the output driver of FIG. 5;
- [0015] FIGS. 7B, 8B, 9B, and 10B illustrate embodiments of operating signals for the output drivers of FIGS. 7A, 8A, 9A, and 10A, respectively;
- [0016] FIG. 11 illustrates an embodiment of data signals and operation speeds for an output driver;
- [0017] FIG. 12 illustrates an embodiment of a memory block;
- [0018] FIG. 13 illustrates another embodiment of a memory block;
- [0019] FIG. 14 illustrates another embodiment of a memory block; and
- [0020] FIG. 15 illustrates an embodiment of a computing system device.

DETAILED DESCRIPTION

- [0021] FIG. 1 illustrates an embodiment of a non-volatile memory device 1 which may include a memory cell array 20, a row decoder 30, a page buffer circuit 40, a voltage

generator 50, a data input/output circuit 10, and control logic 60. The non-volatile memory device 1 may include other or different features in another embodiment.

[0022] The non-volatile memory device 1 may include a NAND flash memory, a vertical NAND (VNAND) flash memory, a NOR flash memory, resistive random-access memory (RRAM), phase-change random-access memory (PRAM), magnetoresistive random-access memory (MRAM), ferroelectric random-access memory (FRAM), spin-transfer torque random-access memory (STT-RAM), or another type of memory. The non-volatile memory device 1 may have a three-dimensional array structure. For convenience of explanation, the non-volatile memory device 1 will be described as a NAND flash memory device.

[0023] The memory cell array 20 may include a plurality of memory blocks. Each memory block may include a plurality of memory cells. Some of the plurality of memory cells may be, for example, single level cells (SLCs), each storing 1-bit data. Other memory cells may be multi-level cells (MLCs).

[0024] The memory cell array 20 may be connected to the row decoder 30 through word lines WLs, string select lines SSLs, and ground select lines GSLs and may be connected to the page buffer circuit 40 through bit lines BLs. The memory cell array 20 may include strings connected to the bit lines BLs. Each of the strings may include at least one string select transistor, a plurality of memory cells, and at least one ground select transistor connected in series between a bit line and a common source line CSL. Each of the strings may further include at least one dummy cell between the string select transistor and the plurality of memory cells, and may further include at least one dummy cell between the ground select transistor and the plurality of memory cells.

[0025] FIG. 1 shows that the non-volatile memory device 1 includes one memory cell array 20. In one embodiment, the non-volatile memory device 1 may include a plurality of memory cell arrays 20.

[0026] The row decoder 30 may select some of the word lines WLs based on a row address X-ADDR. The row decoder 30 may provide a word line voltage to a word line. During a program operation, the row decoder 30 may apply a program voltage and a verify voltage to a selected word line, and may apply a program inhibit voltage to an unselected word line. During a read operation, the row decoder 30 may apply a read voltage to a selected word line and apply a read inhibit voltage to an unselected word line. Furthermore, the row decoder 30 may select some of the string select lines SSL or some of the ground select lines GSL based on the row address X-ADDR.

[0027] The page buffer circuit 40 may be connected to the memory cell array 20 through the bit lines BLs and may perform a program operation or a read operation based on a page buffer control signal CTRL_PB received from the control logic 60. The page buffer circuit 40 may be connected to data lines DLs by selecting the bit lines BLs by using a decoded column address.

[0028] The page buffer circuit 40 may include a plurality of page buffers for storing data to be programmed during a program operation or storing data to be read out during a read operation. Each of the plurality of page buffers may include a plurality of latches. During a program operation, data stored in the plurality of page buffers may be programmed into a page corresponding to a selected memory block through the bit lines BLs. During a read operation, data read out from a page corresponding to a selected memory block may be stored in the plurality of page buffers through the bit lines BLs. The page buffer circuit 40 may read data from a first area of the memory cell array 20 and

store the read data in a second area of the memory cell array 20. The page buffer circuit 40 may perform, for example, a copy-back operation.

[0029] The voltage generator 50 may generate various types of voltages for performing a program operation, a read operation, and an erase operation with regard to the memory cell array 20 based on a voltage control signal CTRL_vol. For example, the voltage generator 50 may generate a word line operating voltage VWL to operate the word lines WLs. At this time, a first operating voltage VWL may be a program voltage (or a write voltage), a read voltage, an erase voltage, an inhibit voltage, or a program verify voltage. The voltage generator 50 may further generate a string select line operating voltage VSLL for operating a plurality of string select lines SSL and a ground select line operating voltage VGSL for operating a plurality of ground select lines GSL.

[0030] The control logic 60 may output various internal control signals for storing data in the memory cell array 20 or reading out data from the memory cell array 20, based on a command CMD, an address ADDR, and a control signal CTRL received from a memory controller. The control logic 60 may control the overall operations of the internal components of the non-volatile memory device 1. Various internal control signals output from the control logic 60 may be provided to the row decoder 30, the voltage generator 50, the page buffer circuit 40, and the data input/output circuit 10. For example, the control logic 60 may provide a row address X-ADDR to the row decoder 30, a voltage control signal CTRL_vol to the voltage generator 50, a page buffer control signal CTRL_PB to the page buffer circuit 40, and an output control signal CTRL_O to the data input/output circuit 10. In one embodiment, the control logic 60 may provide these and/or other internal control signals. For example, the control logic 60 may provide a column address

to a column decoder. The control logic 60 may further include a clock signal generator that generates a clock signal.

[0031] The control logic 60 may provide an output control signal CTRL_O to the data input/output circuit 10. The output control signal CTRL_O may include information regarding a level of a power supply voltage used in the non-volatile memory device 1 and information regarding an operating frequency of the non-volatile memory device 1 (e.g., a clock signal).

[0032] The data input/output circuit 10 may be connected to at least one page buffer circuit 40 via the data lines DLs. During a data read operation, the data input/output circuit 10 may output read data to the page buffer circuit 40 to an external destination through the data lines DLs.

[0033] The data input/output circuit 10 may include a data output circuit 100 that operates according to the output control signal CTRL_O output by the control logic 60. The data output circuit 100 may transmit a data signal DQ to a memory controller.

[0034] FIG. 2 illustrates an embodiment of a data output circuit 100, which may be an example of the data output circuit 10 of FIG. 1.

[0035] Referring to FIGS. 1 and 2, the data output circuit 100 may include an output driver 110 and an operating signal generator 120. The data output circuit 100 may receive internal data DATA via the data lines DLs and receive a clock signal CLK from the control logic 60. The data output circuit 100 may receive internal data DATA and output the data signal DQ under the control of the control logic 60. The data signal DQ may have high and low levels depending on the clock signal CLK and internal data DATA. The data signal DQ may be an AC-type signal swinging between a high-level output voltage and a low-level output voltage.

[0036] The output driver 110 may include a pull-up driver 111 for generating a current determined according to a pull-up operating signal OP_U and a pull-down driver 113 having a resistance determined according to a pull-down operating signal OP_D. The pull-up driver 111 may include a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors. The pull-down driver 113 may include a pull-down transistor including a plurality of N-type transistors.

[0037] The operating signal generator 120 may output the pull-up operating signal OP_U and the pull-down operating signal OP_D based on the internal data DATA and the clock signal CLK. The pull-up operating signal OP_U may be a code for changing a current generated by the pull-up driver 111 of the output driver 110. The pull-down operating signal OP_D may be a code for changing an amount of a current flowing to the pull-down driver 113 of the output driver 110. Therefore, the ON resistance of the output driver 110 may be adjusted according to the pull-up operating signal OP_U and the pull-down operating signal OP_D.

[0038] The pull-up driver 111 and the pull-down driver 113 may be turned ON alternately. When the pull-up driver 111 is operating, a high-level data signal DQ may be output. When the pull-down driver 113 is operating, a low-level data signal DQ may be output. For example, the operating signal generator 120 may generate the pull-up operating signal OP_U capable of turning ON all transistors in the pull-up driver 111 and, at the same time, generate the pull-down operating signal OP_D capable of turning OFF all transistors in the pull-down driver 113.

[0039] For example, when the output driver 110 outputs the data signal DQ, the operating signal generator 120 may change the amount of each current flowing to the pull-

up driver 111 and the pull-down driver 113, thereby determining respective resistances of the pull-up driver 111 and the pull-down driver 113.

[0040] FIG. 3 illustrates a circuit embodiment of the output driver 110 of FIG. 2, which may include the pull-up driver 111 and the pull-down driver 113.

[0041] The pull-up driver 111 may include a first pull-up driver PU connected between a first power supply voltage VDDQ_P and a node N and a second pull-up driver NU connected between a second power supply voltage VDDQ_N and the node N. At this time, the first power supply voltage VDDQ_P and the second power supply voltage VDDQ_N may have a same level or may have different levels. For example, the voltage level of the first power supply voltage VDDQ_P may be higher than that of the second power supply voltage VDDQ_N.

[0042] The first pull-up driver PU may include 0^{th} through k^{th} pull-up transistors PU0 through PUK. In this case, k is a natural number. The 0^{th} through k^{th} pull-up transistors PU0 through PUK of the first pull-up driver PU may be implemented as P-type transistors.

[0043] The second pull-up driver NU may include the 0^{th} through l^{th} pull-up transistors NU0 through NUL. In this case, l is a natural number. The 0^{th} through l^{th} pull-up transistors NU0 through NUL of the second pull-up driver NU may be implemented as N-type transistors, respectively.

[0044] The pull-down driver 113 may include 0^{th} through m^{th} pull-down transistors ND0 through NDm connected between a ground voltage VSS and the node N, where m is a natural number. The 0^{th} through m^{th} pull-down transistors ND0 through NDm may be implemented as N-type transistors.

[0045] The pull-up driver 111 may generate a current determined according to the pull-up operating signal OP_U. The first pull-up driver PU and the second pull-up driver NU

may receive the pull-up operating signal OP_U from the operating signal generator 120. As a result, ON and OFF states of k transistors and l transistors may be adjusted. An amount of current flowing through the pull-up driver 111 may be adjusted depending on ON and OFF states of the k transistors in the first pull-up driver PU and the l transistors included in the second pull-up driver NU.

[0046] The pull-up operating signal OP_U includes a plurality of first pull-up operating signals OP_PU0 through OP_PUk input to the 0th through kth pull-up transistors PU0 through PUk of the first pull-up driver PU and a plurality of second pull-up operating signals OP_NU0 through OP_NUl input to the 0th through lth pull-up transistors NU0 through NUl of the second pull-up driver NU.

[0047] When the plurality of second pull-up operating signals OP_NU0 through OP_NUl are at the high level, the voltage levels of the second pull-up operating signals OP_NU0 through OP_NUl may be identical to that of the second power supply voltage VDDQ_N. In one embodiment, each of the voltage levels of the plurality of second pull-up operating signals OP_NU0 through OP_NUl when the plurality of second pull-up operating signals OP_NU0 through OP_NUl are at the high level may be higher than that of the second power supply voltage VDDQ_N. For example, the plurality of second pull-up operating signals OP_NU0 through OP_NUl may be generated based on a voltage, which is generated by a voltage generator (e.g., the voltage generator 50 in FIG. 1) in a non-volatile memory device and boosted, or a voltage input from an external device (e.g., a memory controller).

[0048] The ON and OFF states of the 0th through mth transistors ND0 through NDm may be switched according to the pull-down operating signal OP_D input to the pull-down driver 113. The pull-down operating signal OP_D may include a plurality of pull-

down operating signals OP_ND0 through OP_NDm respectively input to the 0th through mth pull-down transistors ND0 through NDm. Furthermore, an amount of a current flowing in the pull-down driver 113 may be adjusted according to the ON/OFF state of each of the m transistors. Therefore, as each of the currents flowing to the pull-up driver 111 and the pull-down driver 113 is adjusted, the output driver 110 may have a specific resistance corresponding to the current, and the data signal may be transmitted to a memory controller via a DQ pad.

[0049] When the plurality of pull-down operating signals OP_ND0 through OP_NDm are at the high level, each of the voltage levels of the plurality of pull-down operating signals OP_ND0 through OP_NDm may be identical to that of the first power supply voltage VDDQ_P or the second power supply voltage VDDQ_N. In one embodiment, each of the voltage levels of the plurality of second pull-down operating signals OP_ND0 through OP_NDm, when the plurality of second pull-down operating signals OP_ND0 through OP_NDm are at the high level, may be higher than those of the first power supply voltage VDDQ_P and the second power supply voltage VDDQ_N. For example, the plurality of second pull-down operating signals OP_ND0 through OP_NDm may be generated based on a voltage (which is generated by a voltage generator in a non-volatile memory device and boosted) or a voltage input from an external device (e.g., a memory controller).

[0050] In an example embodiment, the pull-up driver 111 includes the first pull-up driver PU including P-type transistors and the second pull-up driver NU including N-type transistors. A range of levels of a power supply voltage VCCQ used for operating the pull-up driver 111 may be widened.

[0051] Furthermore, since the pull-up driver 111 includes both the P-type transistors and the N-type transistors, a current generated by the pull-up driver 111 with respect to a data output voltage VDQ of the DQ pad connected to the node N may be linear as a result of characteristics of the P-type transistors and the N-type transistors.

[0052] FIGS. 4A and 4B illustrate circuit embodiments for comparing and describing operating mechanisms of a pull-up driver according to voltage levels of a power supply voltage.

[0053] Referring to FIG. 4A, the pull-up driver 111 may include the first pull-up driver PU including P-type transistors PU0 through PUK and the second pull-up driver NU including N-type transistors NU0 through NUL. Low power supply voltages VDDQ1 having a same voltage level may be applied to the first pull-up driver PU and the second pull-up driver NU, respectively. A low power supply voltage VDDQ1 may refer to a power supply voltage having a relatively low voltage level, and in one embodiment, may have a voltage level lower than that of a high power supply voltage VDDQ2 of FIG. 4B described below.

[0054] For the P-type transistors PU0 through PUK to be turned ON, due to characteristics of P-type transistors, differences between the voltage level of the low power supply voltage VDDQ1 and the voltage levels of the plurality of first pull-up operating signals OP_PU0 through OP-PUK input to turn ON the P-type transistors PU0 through PUK may be greater than the respective threshold voltages of the P-type transistors PU0 through PUK. The threshold voltages of the P-type transistors PU0 through PUK may vary according to recipes of processes for fabricating the respective P-type transistors PU0 through PUK. The threshold voltages of the P-type transistors PU0 through PUK may differ from one another. Therefore, when the low power supply voltage

VDDQ1 having a relatively low voltage level is applied, at least some of the P-type transistors PU0 through PUK may not be turned ON.

[0055] The N-type transistors NU0 through NU1 may be normally turned ON even when the low power supply voltage VDDQ1 having a voltage level lower than a certain level is applied, because conditions for turning ON the N-type transistors NU0 through NU1 are satisfied.

[0056] Therefore, even when a relatively low power supply voltage (e.g., the low power supply voltage VDDQ1) is applied to the pull-up driver 111 in the non-volatile memory device according to an example embodiment and a current ID_PU1 output by the first pull-up driver PU is insufficient, the current ID_PU1 may be supplemented by a current ID_NU1 output by the second pull-up driver NU.

[0057] Referring to FIG. 4B, the high power supply voltage VDDQ2 having a relatively high voltage level may be applied to the pull-up driver 111. The high power supply voltages VDDQ2 having a same voltage level may be applied to the first pull-up driver PU and the second pull-up driver NU, respectively. The high power supply voltage VDDQ2 may refer to a power supply voltage having a relatively high voltage level, and in one embodiment, may have a voltage level higher than that of the low power supply voltage VDDQ1 of FIG. 4A.

[0058] For the N-type transistors NU0 through NU1 to be turned ON, due to characteristics of N-type transistors, differences between the voltage levels of the plurality of second pull-up operating signals OP_NU0 through OP-NU1 input to turn ON the N-type transistors NU0 through NU1 and the voltage level of the data signal DQ may be greater than the respective threshold voltages of the N-type transistors NU0 through NU1.

When the high power supply voltage VDDQ2 having a relatively high voltage level is applied, at least some of the N-type transistors NU0 through NU1 may not be turned ON.

[0059] The P-type transistors PU0 through PUK may be normally turned ON even when the high power supply voltage VDDQ2 having a voltage level equal to or higher than a certain level is applied, because conditions for turning ON the P-type transistors PU0 through PUK are satisfied.

[0060] Therefore, even when a relatively high power supply voltage (e.g., the high power supply voltage VDDQ2 is applied to the pull-up driver 111 in the non-volatile memory device according to an example embodiment and a current ID_PU2 output by the second pull-up driver NU is insufficient, the current ID_PU2 may be supplemented by a current ID_PU2 output by the first pull-up driver NU.

[0061] A case where the power supply voltages VDDQ1 and VDDQ2 having a same voltage level are applied to the first pull-up driver PU and the second pull-up driver NU is described with reference to FIGS. 4A and 4B. In one embodiment, for example, power supply voltages having different voltage levels may be applied to the first pull-up driver PU and the second pull-up driver NU, respectively. For example, the high power supply voltage VDDQ2 may be applied to the first pull-up driver PU, and the low power supply voltage VDDQ1 may be applied to the second pull-up driver NU.

[0062] The low power supply voltage VDDQ1 and the high power supply voltage VDDQ2 applied to the pull-up driver 111 are merely examples. In one embodiment, power supply voltages having voltage levels of a wide range including the low power supply voltage VDDQ1 having a relatively low voltage level and the high power supply voltage VDDQ2 having a relatively high voltage level may be applied to the pull-up driver 111 in a non-volatile memory device according to an example embodiment.

[0063] Due to differences between characteristics of the P-type transistors PU0 through PUK and characteristics of the N-type transistors NU0 through NUI, curves (not shown) indicating changes of currents ID_PU and ID_NU respectively flowing to the P-type transistors PU0 through PUK and the N-type transistors NU0 through NUI according to the data output voltage VDQ, which is the voltage level of the data signal DQ, may differ from each other.

[0064] The overall current ID_U flowing to the pull-up driver 111 is a sum of the current ID_PU flowing to the P-type transistors PU0 through PUK and the current ID_NU flowing to the N-type transistors NU0 through NUI. Since the pull-up driver 111 includes both the P-type transistors PU0 through PUK and the N-type transistors NU0 through NUI, the current ID_U flowing to the pull-up driver 111 with respect to the output voltage VDQ may be linear. Therefore, the output driver 110, which includes the pull-up driver 111, may have a constant AC ON-resistance.

[0065] FIG. 5 illustrates another embodiment of the output driver 110 of FIG. 2. In an example, the magnitude of currents flowing to P-type transistors and N-type transistors in a pull-down driver changes according to data output voltages. Compared with the pull-down driver 113 of FIG. 3, a pull-down driver 113a may further include a plurality of P-type transistors.

[0066] Referring to FIGS. 2 and 5, the output driver 110 may include the pull-up driver 111 and the pull-down driver 113a. The pull-down driver 113a may include a first pull-down driver PD and a second pull-down driver ND connected between the ground voltage VSS and the node N. The first pull-down driver PD may include 0th through nth pull-down transistors PD0 through PDn, where n is a natural number. Each of the 0th through nth pull-down transistors PD0 through PDn may be a P-type transistor. The second pull-down

driver ND may include 0^{th} through m^{th} pull-down transistors ND0 through NDm, where m is a natural number. Each of the 0^{th} through m^{th} pull-down transistors ND0 through NDm may be implemented as an N-type transistor.

[0067] When the internal data DATA is at a low level, the pull-down driver 113a may have a particular resistance value based on the pull-down operating signal OP_D. The pull-down operating signal OP_D may include a plurality of first pull-down operating signals OP_PD0 through OP_PDn input to the 0^{th} through n^{th} pull-down transistors PD0 through PDn of the first pull-down driver PD, and a plurality of second pull-down operating signals OP_ND0 through OP_NDm input to the 0^{th} through m^{th} pull-down transistors ND0 through NDm of second pull-down driver ND.

[0068] Referring to FIG. 5, due to differences between characteristics of the P-type transistors PD0 through PDn and characteristics of the N-type transistors ND0 through NDm, curves (not shown) indicating changes of currents ID_PD and ID_ND respectively flowing to the P-type transistors PD0 through PDn and the N-type transistors ND0 through NDm according to the data output voltage VDQ may differ from each other.

[0069] A current ID_D flowing to the pull-down driver 113a is a sum of the current ID_PD flowing to the P-type transistors PD0 through PDn and the current ID_ND flowing to the N-type transistors ND0 through NDm. Since the pull-down driver 113a includes both the P-type transistors PD0 through PDn and the N-type transistors ND0 through NDm, the current ID_D flowing to the pull-down driver 113a with respect to the data output voltage VDQ may be linear. The output driver 110a including the pull-up driver 111 and the pull-down driver 113a may have a constant AC ON-resistance.

[0070] FIG. 6 illustrates another example embodiment of the data output circuit 100b of FIG. 1. Referring to FIG. 6, a data output circuit 100b may include an output driver 110b

and an operating signal generator 120b. The data output circuit 100b may receive internal data DATA via data lines (e.g., the data lines DLs in FIG. 1) and, based on the internal data DATA, output the data signal DQ under the control of a control logic (e.g., control logic 60 of FIG. 1).

[0071] The output driver 110b includes a pull-up driver 111b for generating a current determined according to pull-up operating signals OP_PU and OP_NU and a pull-down driver 113b having resistance determined based on pull-down signals OP_PD and OP_ND. The pull-up driver 111b may include a first pull-up driver including a plurality of P-type transistors and a second pull-up driver including a plurality of N-type transistors. The pull-down driver 113b may include a first pull-down driver including a plurality of P-type transistors and a second pull-down driver including a plurality of N-type transistors. The output driver 110b may have, for example, the same configuration as the output driver 110a of FIG. 5.

[0072] The operating signal generator 120b may output pull-up operating signals OP_PU and OP_NU and pull pull-down signals OPD_PD and OP_ND based on the internal data DATA and the information regarding a power supply voltage VCCQ MODE applied to the pull-up driver 111b. The information regarding a power supply voltage VCCQ MODE may be included in an output control signal (e.g., the output control signal CTRL_O) from a control logic (e.g., the control logic 60 in FIG. 1).

[0073] The pull-up operating signals OP_PU and OP_NU may include a first pull-up operating signal OP_PU and a second pull-up operating signal OP_NU. The first pull-up operating signal OP_PU may be an operating signal for operating the first pull-up driver and the second pull-up operating signal OP_NU may be an operating signal for operating the second pull-up driver.

[0074] The pull-down operating signals OP_PD and OP_ND may include a first pull-down operating signal OP_PD and a second pull-down operating signal OP_ND. The first pull-down operating signal OP_PD may be an operating signal for operating the first pull-down driver. The second pull-down operating signal OP_ND may be an operating signal for operating the second pull-down driver.

[0075] The operating signal generator 120b may selectively turn OFF one of the first pull-up driver and the second pull-up driver in the pull-up driver 111b and may generate pull-up operating signals OP_PU and OP_NU corresponding thereto. Furthermore, the operating signal generator 120b may selectively turn OFF one of the first pull-down driver and the second pull-down driver in the pull-down driver 113b and may generate pull-down operating signals OP_PD and OP_ND corresponding thereto.

[0076] FIG. 7A illustrates an embodiment of the output driver of FIG. 5 which includes four equivalent transistors which are all operated. FIG. 7B illustrates an embodiment of a timing diagram including operating signals that may be input into the output driver of FIG. 7A.

[0077] Referring to FIGS. 6, 7A, and 7B, the first pull-up driver PU of the pull-up driver 111b may be indicated as one equivalent P-type transistor, and the second pull-up driver NU may be indicated as one equivalent N-type transistor. The first pull-down driver PD of the pull-down driver 113b may be indicated as one equivalent P-type transistor. The second pull-down driver ND may be indicated as one equivalent N-type transistor.

[0078] The operating signal generator 120b may output the pull-up operating signals OP_PU and OP_NU and the pull-down operating signals OP_PD and OP_ND based on the internal data DATA and a code regarding the information regarding a power supply voltage VCCQ MODE applied to the pull-up driver 111b and an output driver 110b.

[0079] According to an example embodiment, when power supply voltages applied to the first pull-up driver PU and the second pull-up driver NU respectively satisfy conditions for the first pull-up driver PU and the second pull-up driver NU to be normally operated, the operating signal generator 120b may generate pull-up operating signals OP_PU and OP_NU toggling between a high level H and a low level L based on the internal data DATA. Furthermore, the operating signal generator 120b may generate pull-down operating signals OP_PD and OP_ND toggling between the high level H and the low level L.

[0080] Therefore, current flowing to the pull-up driver 111b and current flowing to the pull-down driver 113b with respect to the data output voltage VDQ may be linear.

[0081] In one embodiment, when the operating signal generator 120b generates an operating signal toggling between the high level H and the low level L, the operating signal generator 120b operates the pull-up driver 111b or the pull-down driver 113b that receives the toggling operating signal. For example, when the operating signal generator 120b generates an operating signal toggling between the high level H and the low level L with respect to at least one of the plurality of P-type transistors in the first pull-up driver PU, the operating signal generator 120b may be considered to operate the first pull-up driver PU. The same description may be applied to the second pull-up driver NU, the first pull-down driver PD, and the second pull-down driver ND.

[0082] FIG. 8A illustrates another embodiment of the output driver of FIG. 5 which includes four equivalent transistors, one or more of which are not operated. FIG. 8B illustrates an embodiment of a timing diagram including operating signals input to the output driver of FIG. 8A.

[0083] Referring to FIGS. 6, 8A and 8B, the operating signal generator 120b may selectively operate at least one of the first pull-up driver PU and the second pull-up driver PU of the pull-up driver 111b. For example, the operating signal generator 120b may output a pull-up operating signal OP_PU or OP_NU to one of the first pull-up driver PU and the second pull-up driver NU to turn OFF the first pull-up driver PU or the second pull-up driver NU.

[0084] The operating signal generator 120b may selectively operate at least one of the first pull-down driver PD and the second pull-down driver ND of the pull-down driver 113b. For example, the operating signal generator 120b may output a pull-down operating signal OP_PD or OP_ND to one of the first pull-down driver PD and the second pull-down driver ND to turn OFF the first pull-down driver PD or the second pull-down driver ND.

[0085] When power supply voltages applied to the first pull-up driver PU and the second pull-up driver NU respectively satisfy conditions for the first pull-up driver PU and the second pull-up driver NU to be normally operated, the operating signal generator 120b may generate pull-up operating signals OP_PU and OP_NU toggling between the high level H and the low level L based on the internal data DATA.

[0086] The operating signal generator 120b may normally operate only the second pull-down driver ND from between the first pull-down driver PD and the second pull-down driver ND. Based on the internal data DATA, the operating signal generator 120b may generate the second pull-down operating signal OP_ND toggling between the high level H and the low level and the first pull-down operating signal OP_PD having the high level H. Therefore, the power consumption at the output driver 110b may be reduced. In some cases, the operating signal generator 120b may normally operate only the first pull-down

driver PD from between the first pull-down driver PD and the second pull-down driver ND.

[0087] FIG. 9A illustrates another embodiment of the output driver of FIG. 5 which includes four equivalent transistors, where some of the four equivalent transistors are not operated. FIG. 9B illustrates an embodiment of a timing diagram which includes operating signals input to the output driver of FIG. 9A.

[0088] Referring to FIGS. 6, 9A and 9B, a power supply voltage applied to the second pull-up driver NU may satisfy a condition for the second pull-up driver NU to operate normally, but a power supply voltage applied to the PU may not satisfy a condition for the first pull-up driver PU to operate normally. For example, the low power supply voltage VDDQ1 of FIG. 4A may be applied to first pull-up driver PU. The operating signal generator 120b may normally operate only the second pull-up driver NU from between the first pull-up driver PU and the second pull-up driver NU in the output driver 110b. Therefore, the operating signal generator 120b may generate the second pull-up operating signal OP_NU toggling between the high level H and the low level L based on the internal data DATA, and may generate the first pull-up operating signal OP_PU having the high level H. Since only the second pull-up driver NU is normally operated, power consumed by the output driver 110b may be reduced.

[0089] In one embodiment, when a power supply voltage applied to the second pull-up driver NU does not satisfy a condition for the second pull-up driver NU to operate normally (e.g., when the high power supply voltage VDDQ2 of FIG. 4B is applied to second pull-up driver NU), the operating signal generator 120b may generate the first pull-up operating signal OP_PU toggling between the high level H and the low level L

based on the internal data DATA, and may generate the second pull-up operating signal OP_NU having the low level L.

[0090] The operating signal generator 120b may generate the pull-down operating signals OP_PD and OP_ND toggling between the high level H and the low level L, such that the current ID_D flowing to the pull-down driver 113b with respect to the output voltage VDQ has linearity.

[0091] FIG. 10A illustrates another embodiment of the output driver of FIG. 5 which includes four equivalent transistors, some of which are not operated. FIG. 10B illustrates an embodiment of a timing diagram which includes operating signals input to the output driver of FIG. 10A.

[0092] Referring to FIGS. 6, 10A and 10B, the operating signal generator 120b may selectively operate only one of the first pull-up driver PU and the second pull-up driver NU of the pull-up driver 111b. The operating signal generator 120b may selectively operate only one of the first pull-down driver PD and the second pull-down driver ND of the pull-down driver 113b. Therefore, power consumed by the operating signal generator 120b may be reduced.

[0093] According to an example embodiment, when the low power supply voltage VDDQ1 of FIG. 4A is applied to the operating signal generator 120b, the operating signal generator 120b may only operate the second pull-up driver NU. According to another example embodiment, when the high power supply voltage VDDQ2 of FIG. 4B is applied to the operating signal generator 120b, the operating signal generator 120b may only operate the first pull-up driver (PU).

[0094] Referring to FIGS. 7A through 10B, a data output circuit according to an example embodiment may selectively operate the first pull-up driver PU, the second pull-

up driver NU, the first pull-down driver PD, and the second pull-down driver ND in the output driver 110b. Therefore, the linearity of current flowing to the output driver 110b according to the data output voltage VDQ may be secured, thereby maintaining a constant ON resistance or reducing power consumed by the output driver 110b. In some cases, the first pull-up driver PU, the second pull-up driver NU, the first pull-down driver PD, and the second pull-down driver ND of the output driver 110b may be selectively operated for higher efficiency.

[0095] Examples of the output driver 110b including the first pull-up driver PU, the second pull-up driver NU, the first pull-down driver PD, and the second pull-down driver ND has been described above with reference to FIGS. 7A through 10B. A similar description may be applied to the output driver 110 of FIG. 3.

[0096] FIG. 11 illustrates an embodiment of a timing diagram which includes data signals according to operation speeds that correspond to operation of an output driver.

[0097] Referring to FIGS. 5 and 11, data signals DQ_LF and DQ_HF may have a high level and a low level according to the internal data DATA. The data signals DQ_LF and DQ_HF may be AC-type signals swinging between high-level output voltages VOH_LF and VOH_HF and low-level output voltages VOL_LF and VOL_HF. The data signals DQ_LF and DQ_HF may swing in different forms depending on operation speeds of the data output circuit (e.g., the data output circuit 100 in FIG. 2 or the data output circuit 100b in FIG. 6).

[0098] For example, when a clock signal having a relatively high frequency is input from a control circuit (e.g., the control logic 60 in FIG. 1) to a data output circuit, there may not be enough time for the data signal DQ_HF to swing sufficiently. As a result, a memory controller that receives the data signal DQ_HF may inaccurately determine a

received data value (0 or 1) based on a comparison of the data signal DQ_HF with a reference voltage. Therefore, swinging form of the data signal DQ_HF may improve reliability of the data signal DQ_HF. Termination may be applied to complete the swinging form of the data signal DQ_HF having a high frequency.

[0099] Due to characteristics of an N-type transistor, the level of a source voltage may be less than or equal to a difference between a voltage level of a voltage applied to a gate and a threshold voltage of the N-type transistor. Therefore, as shown in FIGS. 9A, 9B, 10A, and 10B, according to an example embodiment, an operating signal generator (e.g., the operating signal generator 120b of FIG. 6) may operate only the second pull-up driver NU from between the first pull-up driver PU and the second pull-up driver NU. For example, the operating signal generator may generate the second pull-up operating signal OP_NU toggling between a high level voltage H and a low level voltage L based on the internal data DATA and generate the first pull-up operating signal OP_PU having the high level H

[00100] When only the second pull-up driver NU is operated, the voltage level of the data signal DQ_HF may be less than or equal to a difference between the voltage level of the second pull-up operating signal OP_NU and a threshold voltage VTH of an equivalent N-type transistor. Therefore, when the second pull-up operating signal OP_NU is at a high level, the operating signal generator may generate the second pull-up operating signal OP_NU to have a same voltage level as the second power supply voltage VDDQ_N. Thus, an effect for applying termination that reduces the voltage level of the data signal DQ_HF by more than the voltage level of the threshold voltage VTH may occur.

[00101] On the other hand, when a clock signal having a relatively low frequency is input from a control circuit to the data output circuit, the data signal DQ_LF may swing

sufficiently. Therefore, as shown in FIGS. 7A, 7B, 8A, and 8B, the operating signal generator may operate both the first pull-up driver PU and the second pull-up driver NU. In one embodiment, only one of the first pull-up driver PU and the second pull-up driver NU may be operated.

[00102] It has been described above with reference to FIG. 11 that the output driver 110b is operated differently according to operation speeds of the data output circuit. In one embodiment, the aforementioned description may be similarly applied even when an effect of reducing a voltage level of a data signal by more than a voltage level of the threshold voltage V_{TH} level (termination) is to be performed.

[00103] The data output circuit according to an example embodiment may selectively operate the first pull-up driver PU, the second pull-up driver NU, the first pull-down driver PD, and the second pull-down driver ND included therein based on a frequency of a clock signal input to the data output circuit. Therefore, even when high-speed operation is needed, the reliability of a data signal may be maintained.

[00104] FIG. 12 illustrates an embodiment of a memory block. Referring to FIG. 12, a memory cell array (e.g., the memory cell array 20 in FIG. 1) may be a memory cell array of a horizontal NAND flash memory and may include a plurality of memory blocks. Each memory block BLK0 may include m (m is an integer equal to or greater than 2) cell strings STR in which a plurality of memory cells MC are connected in series across bit lines BL0 through BL $m-1$.

[00105] In a NAND flash memory device having the structure as shown in FIG. 12, an erase operation is performed block-by-block and a program operation is performed page-by-page, where pages may correspond to word lines WL0 through WL $n-1$. FIG. 12 illustrates an example in which n pages respectively corresponding to n word lines WL1

through WLn-1 are arranged per block. Furthermore, in one embodiment, the non-volatile memory device 1 of FIG. 1 may include a plurality of memory cell arrays having the same structure and performing the same operation as the memory cell array 20 described above.

[00106] FIG. 13 illustrates another embodiment of a memory block in a memory cell array. Referring to FIG. 13, a memory cell array (the memory cell array 20 in FIG. 1) may be a memory cell array of a vertical NAND flash memory and may include a plurality of memory blocks. Each memory block BLK0' may include a plurality of NAND cell strings NS11 through NS33, a plurality of word lines WL1 through WL8, a plurality of bit lines BL1 through BL3, a plurality of ground select lines GSL1 through GSL3, a plurality of cell string select lines SSL1 through SSL3, and a common source line CSL. FIG. 13 illustrates an example in which eight word lines WL1 through WL8 are arranged in one block. In one embodiment, eight or more word lines may be arranged. The number of NAND cell strings, the number of word lines, the number of bit lines, the number of ground select lines, and the number of cell string select lines may differ among various embodiments.

[00107] NAND cell strings NS11, NS21, and NS31 are between a first bit line BL1 and the common source line CSL. NAND cell strings NS12, NS22, and NS32 are between a second bit line BL2 and the common source line CSL. NAND cell strings NS13, NS23, and NS33 are between a third bit line BL3 and the common source line CSL. Each NAND cell string (e.g., the NAND cell string NS11) may include a cell string select transistor SST, a plurality of memory cells MC1 through MC8, and a ground select transistor GST that are connected in series.

[00108] NAND cell strings connected in common to one bit line constitute one column. For example, the NAND cell strings NS12, NS21, and NS31 connected in common to the

first bit line BL1 may correspond to a first column. The NAND cell strings NS12, NS22, and NS32 connected in common to the second bit line BL2 may correspond to a second column. The NAND cell strings NS13, NS23, and NS33 connected in common to the third bit line BL3 may correspond to a third column.

[00109] NAND cell strings connected to one cell string select line constitute one row. For example, NAND cell strings NS21, NS12, and NS13 connected to a first cell string select line SSL1 correspond to a first row. NAND cell strings NS21, NS22, and NS23 connected to a second cell string select line SSL2 correspond to a second row. NAND cell strings NS31, NS32, and NS33 connected to a third cell string select line SSL3 correspond to a third row.

[00110] Cell string select transistors SST are connected to the corresponding cell string select lines SSL1 through SSL3, respectively. The plurality of memory cells MC1 through MC8 are connected to the corresponding word lines WL1 through WL8, respectively. The ground select transistors GST are connected to the corresponding ground select line GSL1 through GSL3, respectively. The cell string select transistors SST are respectively connected to the corresponding bit lines BL1 through BL3. The ground select transistors GST are connected to the common source line CSL.

[00111] The word lines (e.g., first word lines WL1) at a same level are connected to one another in common. The cell string select lines SSL1 through SSL3 are separated from one another, and the ground select lines GSL1 through GSL3 are also separated from one another. For example, the first word lines WL1 and the first cell string select line SSL1 are selected when memory cells are connected to the first word lines WL1 and belong to the NAND cell string NS11, NS12, and NS13. The ground select lines GSL1 through GSL3 may also be connected to one another in common.

[00112] FIG. 14 illustrates an embodiment of the memory block BLK0 ' of FIG. 13. Referring to FIG. 14, each memory block in a memory cell array (e.g., the memory cell array 20 in FIG. 1) is formed along a direction perpendicular to a substrate SUB. FIG. 14 shows that each memory block includes two select lines GSL and SSL, eight word lines WL1 through WL8, and three bit lines BL1 through BL3. The numbers of these elements may be greater or smaller in other embodiments.

[00113] The substrate SUB has a first conductivity type (e.g., p type), where the common source line CSL extending along a first direction (e.g., the Y direction) and doped with impurities having a second conductivity type (e.g., n type) is provided on the substrate SUB. A plurality of insulation films IL extending along the first direction are sequentially provided along a third direction (e.g., the Z direction) in a region of the substrate SUB between two common source lines CSL adjacent to each other. The plurality of insulation films IL are a particular distance apart from one another along the third direction. For example, the plurality of insulation films IL may include an insulation material, such as a silicon oxide.

[00114] A plurality of pillars P are sequentially arranged along the first direction in a region of the substrate SUB between two adjacent common source lines CSL and penetrate through the plurality of insulation films IL along the first direction. For example, the plurality of pillars P penetrate through the plurality of insulation films IL and contact the substrate SUB. For example, a surface layer S of each pillar P may include, for example, a silicon-based material having a first conductivity type and may function as a channel region. An inner layer I of the each pillar P may include, for example, an insulating material such as but not limited to silicon oxide or an air gap.

[00115] A charge storage layer CS is provided in a region between two adjacent common source lines CSL and along exposed surfaces of the insulation films IL, the plurality of pillars P, and the substrate SUB. The charge storage layer CS may include a gate insulation layer (e.g., also referred to as a 'tunnelling insulation layer'), a charge trapping layer, and a blocking insulation layer. The charge storage layer CS may have, for example, an oxide-nitride-oxide (ONO) structure. Gate electrodes GE including the select lines GSL and SSL and the word lines WL1 through WL8 may be in the region between two adjacent common source lines CSL and on an exposed surface of the charge storage layer CS.

[00116] Drains or drain contacts DR are on the plurality of pillars P, respectively. For example, the drains or drain contacts DR may include a silicon-based material doped with impurities having a second conductivity type. Bit lines BL1 through BL3, which extend along a second direction (e.g., X direction) and are arranged a certain distance apart from one another along the first direction, are provided on the drains DR.

[00117] FIG. 15 illustrates an embodiment of a computing system device 1000 having a non-volatile memory device according any of the embodiments described herein.

[00118] Referring to FIG. 15, the computing system device 1000 may include a CPU 1030, a user interface 1050, a memory controller 1012, and a non-volatile memory device 1010 having the memory controller 1012 and a non-volatile memory device 1011, where the above-stated components are electrically connected to a bus 1060.

[00119] The non-volatile memory device 1010 may include at least one of the data output circuits 100 and 100b of FIGS. 2 and 6 and at least one of the output drivers 110 and 110b of FIGS. 3 and 5. Therefore, the non-volatile memory device 1010 may have a constant ON-resistance, and a power supply voltage having a wide range of voltage levels

may be selectively applied to the output driver. As a result, power consumption may be reduced. The computing system device 1000 may further include a RAM 1040 and a power supply device 1020.

[00120] When the computing system device 1000 is a mobile device, a battery for supplying a voltage for operating the computing system device 1000 and a modem like a baseband chipset may be further provided. Furthermore, the computing system device 1000 may be provided with an application chipset, a camera image processor, a mobile DRAM, etc., detailed description thereof will be omitted.

[00121] The memory controller 1012 and the non-volatile memory device 1011 may constitute a solid state drive/disk SSD using a non-volatile memory for storing data, for example.

[00122] The methods, processes, and/or operations described herein may be performed by code or instructions to be executed by a computer, processor, controller, or other signal processing device. The computer, processor, controller, or other signal processing device may be those described herein or one in addition to the elements described herein. Because the algorithms that form the basis of the methods (or operations of the computer, processor, controller, or other signal processing device) are described in detail, the code or instructions for implementing the operations of the method embodiments may transform the computer, processor, controller, or other signal processing device into a special-purpose processor for performing the methods described herein.

[00123] The voltage generators, controllers, decoders, drivers, and other signal providing, signal generating, and signal processing features of the embodiments described herein may be implemented in non-transitory logic which, for example, may include hardware, software, or both. When implemented at least partially in hardware, the voltage generators,

controllers, decoders, drivers, and other signal providing, signal generating, and signal processing features may be, for example, any one of a variety of integrated circuits including but not limited to an application-specific integrated circuit, a field-programmable gate array, a combination of logic gates, a system-on-chip, a microprocessor, or another type of processing or control circuit.

[00124] When implemented in at least partially in software, the voltage generators, controllers, decoders, drivers, and other signal providing, signal generating, and signal processing features may include, for example, a memory or other storage device for storing code or instructions to be executed, for example, by a computer, processor, microprocessor, controller, or other signal processing device. The computer, processor, microprocessor, controller, or other signal processing device may be those described herein or one in addition to the elements described herein. Because the algorithms that form the basis of the methods (or operations of the computer, processor, microprocessor, controller, or other signal processing device) are described in detail, the code or instructions for implementing the operations of the method embodiments may transform the computer, processor, controller, or other signal processing device into a special-purpose processor for performing the methods described herein.

Example embodiments have been disclosed herein, and although specific terms are employed, they are used and are to be interpreted in a generic and descriptive sense only and not for purpose of limitation. In some instances, as would be apparent to one of skill in the art as of the filing of the present application, features, characteristics, and/or elements described in connection with a particular embodiment may be used singly or in combination with features, characteristics, and/or elements described in connection with other embodiments unless otherwise indicated. Accordingly, various changes in form and

details may be made without departing from the spirit and scope of the embodiments set forth in the claims.

WHAT IS CLAIMED IS:

1. A non-volatile memory device, comprising:
 - an output driver to output a data signal and including:
 - a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors; and
 - a pull-down driver including a plurality of N-type transistors,
 - wherein one or more power supply voltages having different voltage levels are selectively applied to the pull-up driver,
 - wherein a first power supply voltage is applied to the first pull-up driver and a second power supply voltage is applied to the second pull-up driver,
 - wherein the output driver is to be operated based on a pull-up operating signal and a pull-down operating signal received by the output driver, and
 - at least one of the first pull-up driver and the second pull-up driver in the pull-up driver is to be operated based on frequencies of the pull-up operating signal and the pull-down operating signal.
2. The non-volatile memory device as claimed in claim 1, wherein the first power supply voltage is different from the second power supply voltage.
3. The non-volatile memory device as claimed in claim 1, wherein the first power supply voltage is equal to the second power supply voltage.

4. The non-volatile memory device as claimed in any one of claims 1 to 3, wherein the output driver is to operate at least one of the first pull-up driver and the second pull-up driver based on the voltage levels of the first power supply voltage and the second power supply voltage applied to the pull-up driver.

5. The non-volatile memory device as claimed in claim 4, wherein the plurality of P-type transistors of the first pull-up driver are to be turned OFF based on the voltage levels of the first power supply voltage.

6. The non-volatile memory device as claimed in claim 1, wherein the plurality of P-type transistors of the first pull-up driver are to be turned OFF based on frequency of the pull-up operating signal.

7. The non-volatile memory device as claimed in any one of claims 1 to 6, wherein the pull-down driver includes a plurality of P-type transistors.

8. A non-volatile memory device, comprising:
an output driver to output a data signal; and
an operating signal generator to generate a plurality of operating signals for operating the output driver, wherein the output driver includes:

a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors, wherein a first power supply voltage is to be applied to the plurality of P-type transistors of the pull-up driver, and a second power supply voltage is to be applied to the plurality of N-type transistors of the pull-up driver; and

a pull-down driver having a plurality of N-type transistors, wherein one or more power supply voltages having different voltage levels are to be selectively applied to the pull-up driver,

wherein the operating signal generator is to receive information regarding the first power supply voltage and the second power supply voltage applied to the pull-up driver, and,

the operating signal generator is to generate the plurality of operating signals based on the information corresponding to the first power supply voltage and the second power supply voltage.

9. The non-volatile memory device as claimed in claim 8, wherein:

the operating signal generator is to generate at least one operating signal to be transmitted to the first pull-up driver, from among the plurality of operating signals to be toggled between a high level and a low level, and

the operating signal generator is to generate at least one operating signal to be transmitted to the second pull-up driver, from among the plurality of operating signals to be toggled between the high level and the low level.

10. The non-volatile memory device as claimed in claim 8 or claim 9, wherein:

the operating signal generator is to generate operating signals to be respectively transmitted to the plurality of P-type transistors in the first pull-up driver, from among the plurality of operating signals to have a high level,

the operating signal generator is to generate at least one operating signal to be transmitted to the second pull-up driver, from among the plurality of operating signals to be toggled between the high level and a low level, and

a voltage level of the high level of the at least one of operating signal to be transmitted to the second pull-up driver is equal to the voltage level of the second power supply voltage.

11. The non-volatile memory device as claimed in any one of claims 8 to 10, wherein the operating signal generator is to receive a clock signal and generate the plurality of operating signals based on a frequency of the clock signal.

12. The non-volatile memory device as claimed in claim 11, wherein:

the operating signal generator is to generate at least one operating signal to be transmitted to the first pull-up driver, from among the plurality of operating signals to be toggled between a high level and a low level, and

the operating signal generator is to generate at least one operating signal to be transmitted to the second pull-up driver, from among the plurality of operating signals to be toggled between the high level and the low level.

13. The non-volatile memory device as claimed in any one of claims 8 to 12, wherein:

the pull-down driver includes a plurality of P-type transistors,
the plurality of P-type transistors correspond to a first pull-down driver, and
the plurality of N-type transistors correspond to a second pull-down driver.

14. A non-volatile memory device, comprising:
 - an output driver to output a data signal; and
 - an operating signal generator to generate a plurality of operating signals to operate the output driver, wherein the output driver includes:
 - a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors, wherein a first power supply voltage is to be applied to the plurality of P-type transistors of the pull-up driver, and a second power supply voltage is to be applied to the plurality of N-type transistors of the pull-up driver; and
 - a pull-down driver including a first pull-down driver having a plurality of P-type transistors and a second pull-down driver having a plurality of N-type transistors, wherein the operating signal generator is to receive information regarding the first power supply voltage and the second power supply voltage applied to the pull-up driver, and
 - the operating signal generator is to generate the plurality of operating signals based on the information corresponding to the first power supply voltage and the second power supply voltage.

15. The non-volatile memory device as claimed in claim 14, wherein the operating signal generator is to generate a pull-up operating signal to selectively operate at least one of the first pull-up driver and the second pull-up driver and to generate a pull-down operating signal to selectively operate at least one of the first pull-down driver and the second pull-down driver.

16. The non-volatile memory device as claimed in claim 15, wherein the operating signal generator is to selectively operate at least one of the first pull-up driver and the second pull-up driver based on a voltage level of a power supply voltage applied to the pull-up driver.

17. The non-volatile memory device as claimed in claim 15 or claim 16, wherein the operating signal generator is to generate a pull-up operating signal to operate the first pull-up driver and the second pull-up driver and to generate a pull-down operating signal to operate the first pull-down driver and the second pull-down driver.